

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	3893825	bitline or (bit adj line) or contact or drain	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/12 09:45
L2	1912302	1 and (opening or via or viahole or hole or contacthole)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/12 09:50
L3	549692	2 and (transistor or substrate or semiconductor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/12 09:51
L4	180438	3 and gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/12 09:53
L6	391	4 and (SiN or Si ₃ N ₄ or (Si ₃ N ₄ adj N ₃) or ((Si or silicon) adj (nitride)) and conformal ₆)	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/12 09:55

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L16	69505	((bitline or (Bit adj line)) or drain) near20 contact	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/12 12:38
L17	51443	16 and (opening or via or viahole or hole or contacthole)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/12 12:38
L18	47180	17 and (semiconductor or substrate or transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/12 12:39
L19	2403	18 and ((SiN or Si3N4 or (Si ³ adj N ³) or ((Si or silicon) adj (nitride)) and conformal\$6) same (barrier or blanket\$6 or conformal\$6))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/12 12:40
L21	1461	19 and ((polysilicon or ((polycrystalline or poly) adj (Si or silicon))) same (source or drain or source?drain or S?D))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/12 12:42
L22	1337	21 and (@ad<="20030407" or @rlad<="20030407")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/12 12:46

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L1	3893825	bitline or (bit adj line) or contact or drain	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/12 09:45
L2	1912302	1 and (opening or via or viahole or hole or contacthole)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/12 09:50
L3	549692	2 and (transistor or substrate or semiconductor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/12 09:51
L4	180438	3 and gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/12 09:53
L5	19455	4 and (SiN or Si3N4 or (Si ₂ sub\$3 adj N ₂ sub\$3) or ((Si or silicon) adj (nitride)) and conformal\$6)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/12 09:55
L7	17168	5 and (@ad<="20030407" or @rlad<="20030407")	US-PGPUB; USPAT	OR	ON	2005/09/12 10:24
L8	10124	7 and (bitline or (bit adj line) or capacitor or DRAM or SRAM or RAM or FERAM)	US-PGPUB; USPAT	OR	ON	2005/09/12 10:28
L9	9266	8 and (dielectric or insulat\$6 or interlayer or interdielectric or IDL)	US-PGPUB; USPAT	OR	ON	2005/09/12 10:31
L10	9050	9 and (conductive or metal or Ti or TiSi ₂ sub\$3 or polysilicon or titanium)	US-PGPUB; USPAT	OR	ON	2005/09/12 10:37
L11	7785	9 and ((conductive or metal or Ti or TiSi ₂ sub\$3 or polysilicon or titanium or Ti ₂ TiSi ₂ sub\$3) same (remov\$6 or etch\$6 or resist or pattern\$6))	US-PGPUB; USPAT	OR	ON	2005/09/12 10:41
L12	5406	9 and ((conductive or metal or Ti or TiSi ₂ sub\$3 or polysilicon or titanium or Ti ₂ TiSi ₂ sub\$3) same (expos\$6))	US-PGPUB; USPAT	OR	ON	2005/09/12 10:40
L13	5293	11 and 12	US-PGPUB; USPAT	OR	ON	2005/09/12 10:40

L14	4009	9 and ((conductive or metal or Ti or TiSi ₃ or polysilicon or titanium or Ti ₃ Si) same (remov\$6 or etch\$6 or resist or pattern\$6) same source)	US-PGPUB; USPAT	OR	ON	2005/09/12 10:42
L15	3046	13 and 14	US-PGPUB; USPAT	OR	ON	2005/09/12 10:42